

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Docket No.: TIJ-26105

Tomita, et al.

Serial No.: TBD

Art Unit: TBD

Filed: September 1, 1999

Examiner: Not Assigned

Title: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D. C. 20231

"EXPRESS MAIL" mailing label number ELO71335807US, Date of Deposit : September 1, 1999. I hereby certify that the accompanying Application is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the aforementioned date and is addressed to the Assistant Commissioner of Patents, Washington, DC 20231.


Allen B. Kroger

Sir:

Prior to the calculation of the filing fee for the above-identified application, please the amend the application as follows.

IN THE CLAIMS:

Please amend Claims 1-9 as follows:

1. (Amended) Semiconductor device manufacturing method [that includes a process where an] comprising the steps of: providing a semiconductor substrate having an insulating layer formed thereon; etching said insulating layer [on a semiconductor substrate is etched] using a mixed gas of multiple types of fluorocarbon gases that have different ratios of carbon atoms to fluorine atoms (hereafter called C/F ratio).

2. (Amended) Semiconductor device manufacturing method described in Claim 1 [that uses] wherein the [aforementioned] mixed gas [where equal amounts or less of a second fluorocarbon